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## **Electronic Supplementary Information for**

## Journal of Materials Chemistry C

## Novel benzodithiophene unit with alkylthiobiphenyl side chain for

## constructing high-efficiency polymer solar cells

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Fig. S1 TGA plots of PBDTBPS-BDD with a heating rate of 10 °C/min under an inert atmosphere.



Fig. S2 Curves of PBDTBPS-BDD as casted film vs. Fc/Fc<sup>+</sup> in acetonitrile solution.



**Fig. S3** (a) The J-V cures of  $PC_{71}BM$ -based devices with different polymer/  $PC_{71}BM$  ratios (b) The J-V cures of ITIC-based devices with different polymer/ ITIC ratios.



**Fig. S4** (a) The J-V cures of  $PC_{71}BM$ -based devices with different annealing temperature (b) The J-V cures of ITIC-based devices with different annealing temperature.



Fig. S5 (a) The J-V cures of ITIC-based devices with different additive.

|                      | Annealing<br>temperature | additive | Voc  | J <sub>SC</sub>        | FF    | PCE  |
|----------------------|--------------------------|----------|------|------------------------|-------|------|
|                      | (°C)                     | (v/v)    | (∨)  | (mA cm <sup>-2</sup> ) | (%)   | (%)  |
|                      | 100                      | 0.5%DPE  | 0.93 | 16.49                  | 56.83 | 8.72 |
|                      | 100                      | 0.5%DIO  | 0.92 | 14.72                  | 54.61 | 7.44 |
| PBDTBPS-<br>BDD:ITIC | 100                      | 0.5% CN  | 0.92 | 15.17                  | 52.64 | 7.37 |
|                      | 100                      | 1%DPE    | 0.92 | 15.43                  | 54.92 | 7.80 |
|                      | 100                      | 2%DPE    | 0.92 | 14.72                  | 50.64 | 6.86 |

| Device             | $\mu_{\rm e}$ (cm²/Vs) | thickness | $\mu_{ m h}$ (cm²/Vs) | thickness | $\mu_{ m h}/\mu_{ m e}$ |
|--------------------|------------------------|-----------|-----------------------|-----------|-------------------------|
|                    |                        | (nm)      |                       | (nm)      |                         |
| PBDTBPS-BDD:PC71BM | 5.93×10 <sup>-4</sup>  | 120       | 5.25×10 <sup>-4</sup> | 115       | 0.89                    |
| PBDTBPS-BDD:ITIC   | 1.02×10 <sup>-4</sup>  | 100       | 1.45×10 <sup>-4</sup> | 105       | 1.42                    |

 Table S2. The charge carrier mobilities of the optimal blend films.